

Silicon Carbide Diode 22 November 2016

Product data sheet

1. General description

Dual Silicon Carbide Schottky diode in a 3-lead TO-247 plastic package, designed for high frequency switched-mode power supplies.

2. Features and benefits

- Highly stable switching performance
- High forward surge capability IFSM
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

3. Applications

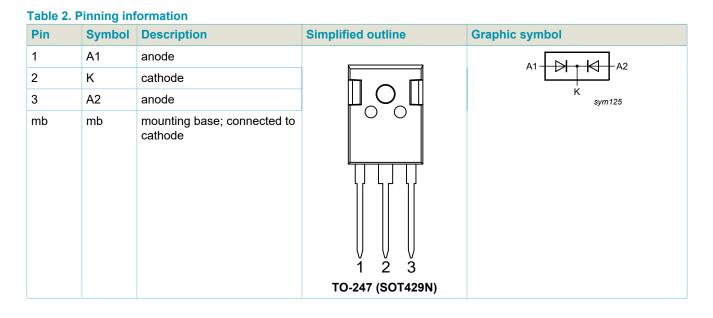
- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- Electrical Vehicle Charger
- Motor Drives

4. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	-	650	V
I _{O(AV)}	limiting average output current	$T_{mb} \le 105 \text{ °C}; \delta_{factor} = 0.5 ; square-wave pulse; both diodes conducting;Fig. 1; Fig. 2; Fig. 3; Fig. 4$	-	-	20	A
Tj	junction temperature		-	-	175	°C
Static chara	acteristics	· · · · · · · · · · · · · · · · · · ·				
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.5	1.7	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.8	2.1	V
Dynamic ch	naracteristics	·	1		1	
Q _r	recovered charge	I _F = 10 A; dI _F /dt = 500 A/μs; V _R = 400 V; T _j = 25 °C; <u>Fig. 7</u>	-	14	-	nC

Silicon Carbide Diode

5. Pinning information



6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
NXPSC20650W	TO-247	Plastic single-ended through-hole package; heatsink mounted; 1 mounting hole; 3-lead TO-247	SOT429N			



7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	650	V
V _{RWM}	crest working reverse voltage		-	650	V
V _R	reverse voltage	DC	-	650	V
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 µs; T _{mb} ≤ 112 °C; square-wave pulse; per diode	-	20	A
I _{O(AV)}	limiting average output current	$T_{mb} \le 105 \text{ °C}; \delta_{factor} = 0.5 ; square-wave pulse; both diodes conducting; Fig. 1; Fig. 2; Fig. 3; Fig. 4$	-	20	A
I _{FSM}	non-repetitive peak forward current	t _p = 10 ms; T _{j(init)} = 25 °C; square-wave pulse; per diode	-	50	A
		t_p = 10 µs; T _{j(init)} = 25 °C; square-wave pulse; per diode	-	450	A
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-	175	°C

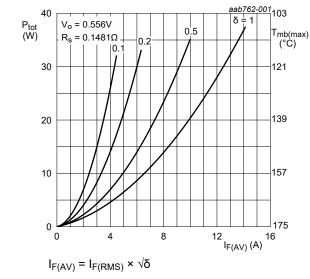


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; per diode

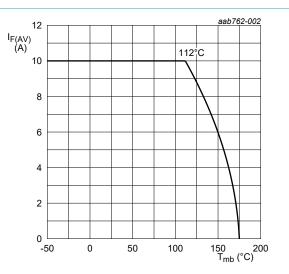
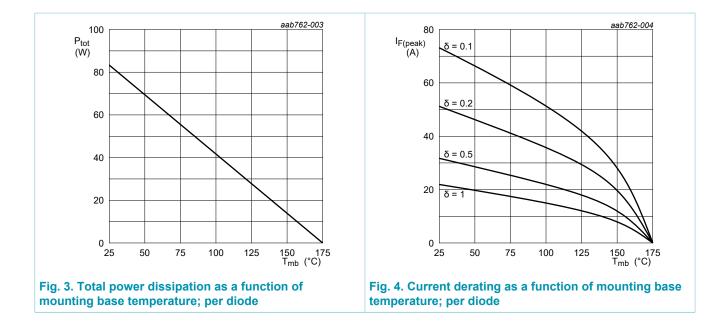


Fig. 2. Forward current as a function of mounting base temperature; per diode

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NXPSC20650W

Silicon Carbide Diode



NXPSC20650W

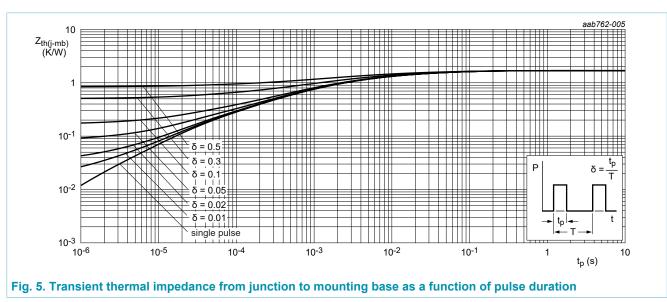
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Silicon Carbide Diode

8. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance	per diode; <u>Fig. 5</u>	-	-	1.8	K/W
	from junction to mounting base	both diodes conducting	-	-	1 K/W	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	45	-	K/W



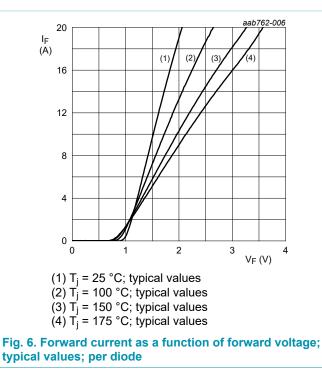


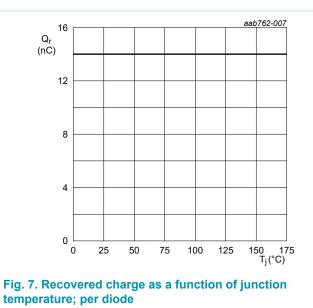
9. Characteristics

Table 6. Characteristics

characteristics are per diode unless otherwise stated

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		· ·			
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.5	1.7	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.8	2.1	V
I _R	reverse current	V _R = 650 V; T _j = 25 °C	-	-	250	μA
		V _R = 650 V; T _j = 150 °C	-	-	800	μA
Dynamic cl	naracteristics	· ·	· ·			
Qr	recovered charge	I _F = 10 A; dI _F /dt = 500 A/µs; V _R = 400 V; T _j = 25 °C; <u>Fig. 7</u>	-	14	-	nC
C _d	diode capacitance	f = 1 MHz; V _R = 1 V; T _j = 25 °C	-	300	-	pF
		f = 1 MHz; V _R = 300 V; T _j = 25 °C	-	32	-	pF
		f = 1 MHz; V _R = 600 V; T _j = 25 °C	-	25	-	pF







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10. Package outline

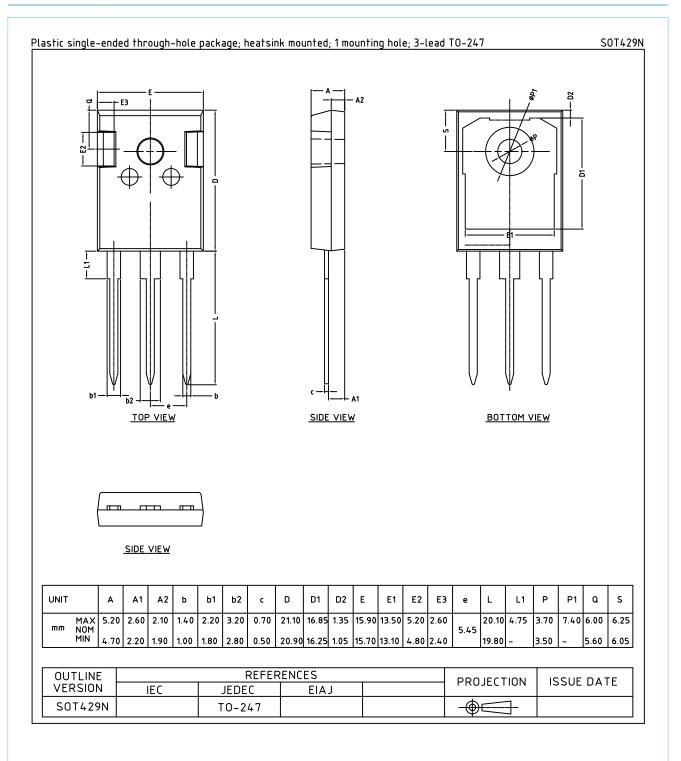


Fig. 8. Package outline TO-247 (SOT429N)

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11. Legal information

Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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NXPSC20650W

12. Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Limiting values	3
8.	Thermal characteristics	5
9.	Characteristics	6
10	Package outline	7
11.	Legal information	8

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